MAX3222E 3V～5.5V マルチチャネル RS-232 ライン ドライバ / レシーバ、±15kV ESD 保護付き

1 特長

- RS-232 バス ピン用 ESD 保護機能
  - ±15kV 人体モデル (HBM)
  - ±8kV IEC61000-4-2、接触放電
  - ±15kV IEC61000-4-2、気中放電
- TIA/EIA-232-F および ITU v.28 規格の要件に適合またはそれを上回る性能
- 3V～5.5V の V_{CC} 電源で動作
- 最大 500kbit/s で動作
- 2 つのドライバと 2 つのレシーバ
- 小さいスタンバイ電流：1µA (標準値)
- 外付けコンデンサ：4 × 0.1µF
- 3.3V 電源で 5V ロジック入力を許容
- SNx5C3222E 向け代替の高速ピン互換デバイス (1Mbit/s)

2 アプリケーション

- 産業用 PC
- 有線ネットワーク
- データ・センターおよびネットワーク機器
- ノート PC
- ハンドヘルド機器

3 概要

MAX3222E は 2 つのライン ドライバ、2 つのライン レシーバ、1 つのデュアル チャージ ポンプ回路で構成されており、ピン間 (シリアル ポート接続ピン、GND を含む) に ±15kV の ESD 保護機能を備えています。

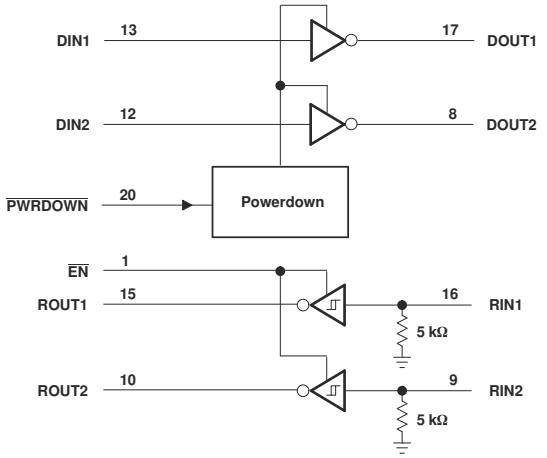
このデバイスは、TIA/EIA-232-F の要件を満たし、非同期通信コントローラとシリアルポート コネクタの間の電気的インターフェイスとして機能します。チャージ ポンプと 4 つの小さな外付けコンデンサにより、3V～5.5V の単一電源で動作できます。本デバイスは最大 500kbit/s のデータ信号速度 (標準値)、最大 30V/µs のドライバ出力スルーレートで動作します。

MAX3222E は、パワーダウン ($\overline{PWRDOWN}$) 入力を Low に設定してパワーダウン モードにすることができます。この状態では電源からわずか 1µA しか流れ込みません。デバイスがパワーダウン モードのとき、ドライバはハイ インピーダンス状態になりますが、レシーバはアクティブのままです。また、パワーダウン モード時には、オンボードのチャージ ポンプがディセーブルになり、V+ が V_{CC} に低下し、V–が GND に向かって上昇します。レシーバの出力 は、イネーブル ($\overline{EN}$) を HIGH に設定することで、高インピーダンス状態に移行することもできます。

パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ(2)
MAX3222E	DB (SSOP、20)	7.2 mm × 7.8mm
	DW (SOIC、20)	12.8 mm × 10.3mm
	PW (TSSOP、20)	6.5 mm × 6.4mm
	DGS (VSSOP、20)	5.1 mm × 4.9mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



ピン番号は、DB、DW、PW パッケージのものです。

論理図 (正論理)

Table of Contents

4 Pin Configuration and Functions

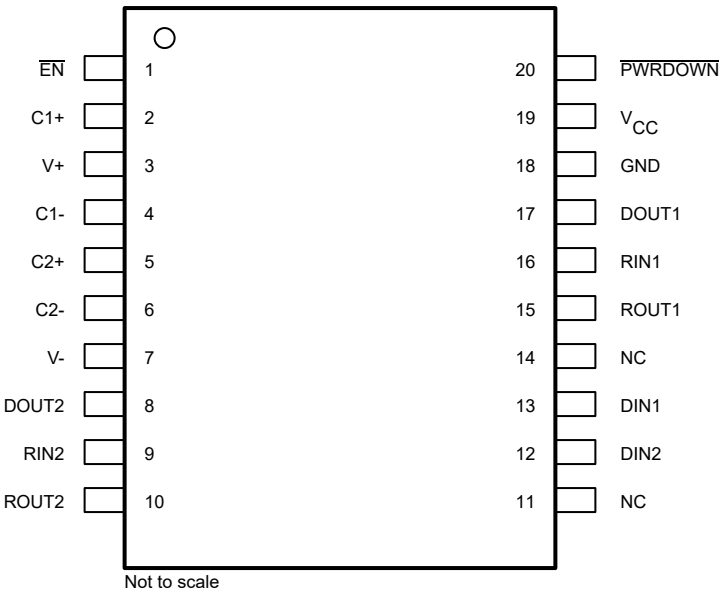


図 4-1. DB, DW, PW DGS Package (Top View)

表 4-1. Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
C1+	2	—	Charge pump capacitor pin
C1-	4	—	Charge pump capacitor pin
C2+	5	—	Charge pump capacitor pin
C2-	6	—	Charge pump capacitor pin
DIN1	13	I	Driver logic input
DIN2	12	I	Driver logic input
DOUT1	17	O	RS-232 driver output
DOUT2	8	O	RS-232 driver output
$\overline{EN}$	1	I	Receiver enable, active low
GND	18	—	Ground
NC	11,14	—	No internal connection
$\overline{PWRDOWN}$	20	I	Driver disable, active low
RIN1	16	I	RS-232 receiver input
RIN2	9	I	RS-232 receiver input
ROUT1	15	O	Receiver logic output
ROUT2	10	O	Receiver logic output
V_{CC}	19	—	Power Supply
V+	3	—	Charge pump capacitor pin
V-	7	—	Charge pump capacitor pin

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range(2)		–0.3	6	V
V+	Positive-output supply voltage range(2)		–0.3	7	V
V–	Negative-output supply voltage range(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage range	Driver ($\overline{EN}$, $\overline{PWRDOWN}$)	–0.3	6	V
		Receiver	–25	25	
V_O	Output voltage range	Driver	–13.2	13.2	V
		Receiver	–0.3	V_{CC} + 0.3	
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.

ESD Ratings

				TYP	UNIT
$V_{(ESD)}$	Electrostatic Discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	All pins except RIN1, RIN2, DOUT1 and DOUT2 pins	±3000	V
			RIN1, RIN2, DOUT1 and DOUT2 pins to GND	±15,000	
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 (2)	All pins	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

ESD Ratings - IEC Specifications

				TYP	UNIT
$V_{(ESD)}$	Electrostatic discharge	IEC 61000-4-2, Contact Discharge(1)	RIN1, RIN2, DOUT1, DOUT2 pins(2)	±8,000	V
		IEC 61000-4-2, Air-Gap Discharge(1)		±15,000	

(1) For PW and DB packages only, a minimum of 1µF capacitor is required between V_{CC} and GND to meet the specified IEC 61000-4-2 rating.
(2) For optimized IEC ESD performance for DGS package, the recommendation is to have series resistor (≥ 50Ω), on all logic inputs directly connected to power or ground, to minimize the transient currents going into or out of the logic pins.

5.2 Recommended Operating Conditions

See 図 8-1 and (1)

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$		0		5.5	V
V_I	Receiver input voltage			–25		25	V
T_A	Operating free-air temperature		MAX3222EC	0		70	°C
			MAX3222EI	–40		85	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

5.3 Thermal Information

THERMAL METRIC(1)		MAX3222E				UNIT
		DB (SSOP)	DW (SOIC)	PW (TSSOP)	DGS (VSSOP)	
		20 Pins	20 Pins	20 Pins	20 Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	91.0	58.0	94.1	92.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	46.2	30.0	35.2	35.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	46.1	29.6	45.5	48.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	12.3	7.7	3.1	1.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	45.6	29.3	45.1	47.7	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC package thermal metrics* application report.

5.4 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 図 8-1)

PARAMETER		TEST CONDITIONS(2)	MIN	TYP(1)	MAX	UNIT
I_I	Input leakage current ($\overline{EN}$, $\overline{PWRDOWN}$)			±0.01	±1	µA
I_{CC}	Supply current	No load, $\overline{PWRDOWN}$ at V_{CC}		0.3	1	mA
	Supply current (powered off)	No load, $\overline{PWRDOWN}$ at GND		1	10	µA

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

5.5 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 図 8-1)

PARAMETER		TEST CONDITIONS(3)		MIN	TYP(1)	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	–5	–5.4		V
I_{IH}	High-level input current	V_I = V_{CC}			±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	µA
I_{OS}	Short-circuit output current(2)	V_{CC} = 3.6 V	V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V					
r_o	Output resistance	V_{CC}, V+, and V– = 0 V,	V_O = ±2 V	300	10M		Ω
I_{OZ}	Output leakage current	$\overline{PWRDOWN}$ = GND	V_{CC} = 3 V to 3.6 V, V_O = ±12 V			±25	µA
			V_{CC} = 4.5 V to 5.5 V, V_O = ±10 V			±25	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
(3) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

5.6 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 図 8-1)

PARAMETER		TEST CONDITIONS(3)		MIN	TYP(1)	MAX	UNIT
	Maximum data rate	C_L = 1000 pF, One DOUT switching,	R_L = 3 kΩ, See 図 6-1	250	500		kbit/s
$t_{sk(p)}$	Pulse skew(2)	C_L = 150 pF to 2500 pF, See 図 6-2	R_L = 3 kΩ to 7 kΩ,		300		ns
SR(tr)	Slew rate, transition region (see 図 6-1)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	6		30	V/µs
			C_L = 150 pF to 2500 pF	4		30	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
(3) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

5.7 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 図 8-1)

PARAMETER		TEST CONDITIONS(2)	MIN	TYP(1)	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
$V_{IT–}$	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis ($V_{IT+} – V_{IT–}$)			0.3		V
I_{OZ}	Output leakage current	$\overline{EN}$ = 1		±0.05	±10	µA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

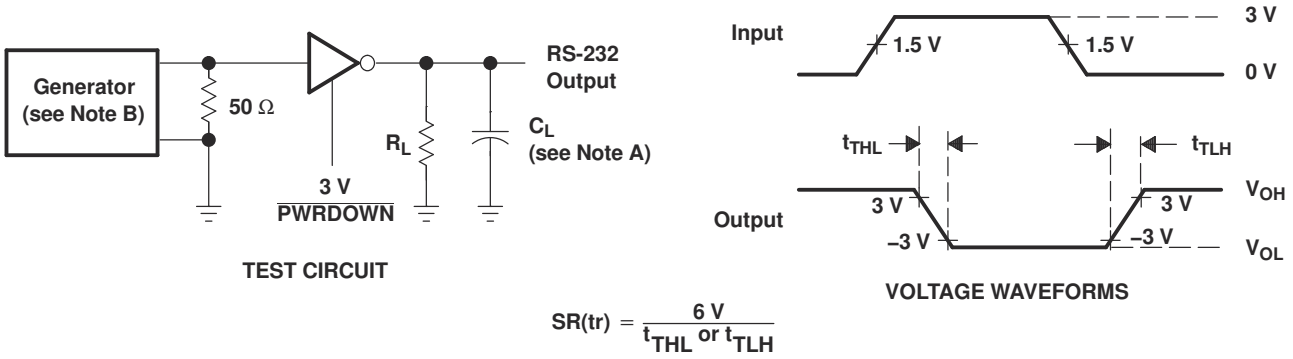
5.8 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS(3)	TYP(1)	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See 図 6-3	300	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See 図 6-3	300	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See 図 6-4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See 図 6-4	200	ns
$t_{sk(p)}$	Pulse skew(2)	See 図 6-3	300	ns

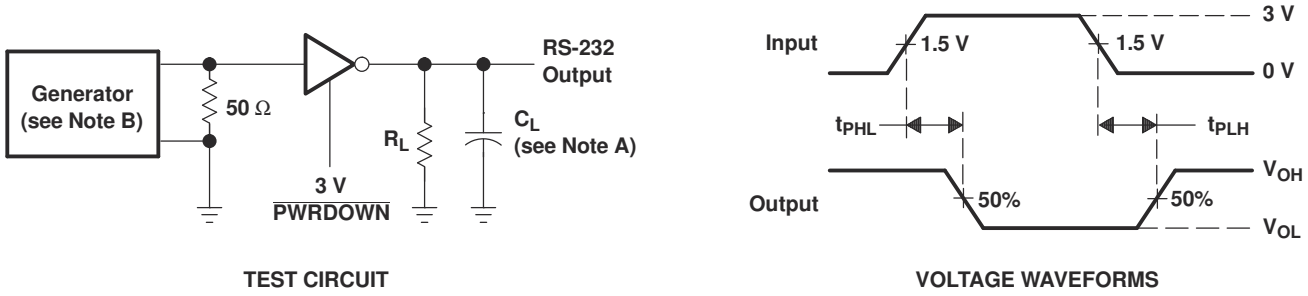
(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(2) Pulse skew is defined as $|t_{PLH} – t_{PHL}|$ of each channel of the same device.
(3) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

6 Parameter Measurement Information



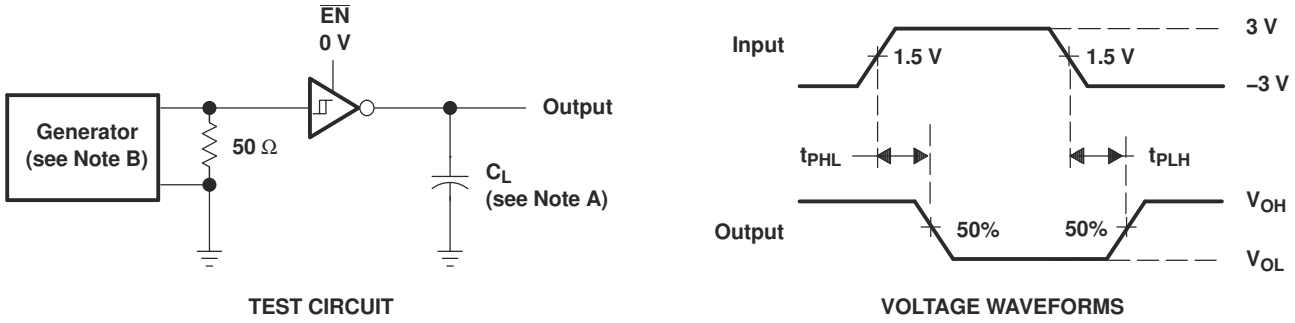
A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250kbit/s, Z_O = 50Ω, 50% duty cycle, t_r ≤ 10ns, t_f ≤ 10ns.

図 6-1. Driver Slew Rate



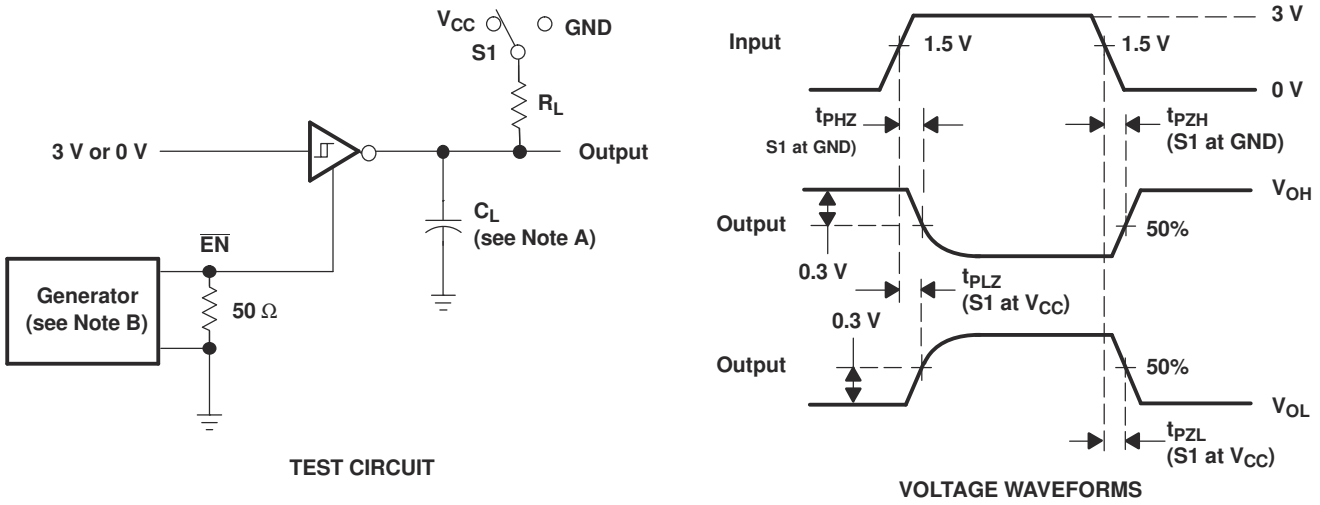
A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250kbit/s, Z_O = 50Ω, 50% duty cycle, t_r ≤ 10ns, t_f ≤ 10ns.

図 6-2. Driver Pulse Skew



A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50Ω, 50% duty cycle, t_r ≤ 10ns, t_f ≤ 10ns.

図 6-3. Receiver Propagation Delay Times



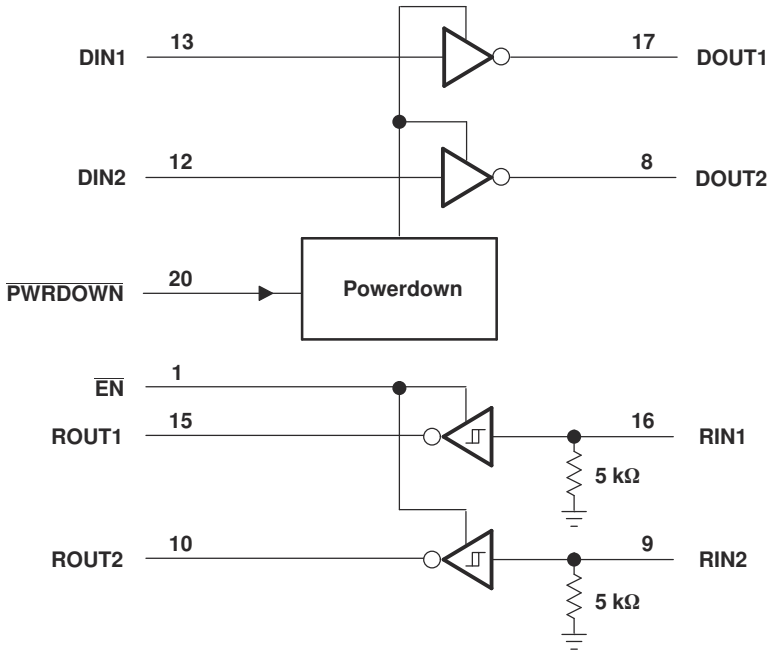
A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50Ω, 50% duty cycle, t_r ≤ 10ns, t_f ≤ 10ns.

図 6-4. Receiver Enable and Disable Times

7 Detailed Description

7.1 Functional Block Diagram



Pin numbers are for the DB, DW, and PW packages.

図 7-1. Logic Diagram (Positive Logic)

7.2 Device Functional Modes

表 7-1. Function Table: Each Driver

INPUTS(1)		OUTPUT DOUT
DIN	PWRDOWN	
X	L	Z
L	H	H
H	H	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

表 7-2. Function Table: Each Receiver

INPUTS(1)		OUTPUT ROUT
RIN	EN	
L	L	H
H	L	L
X	H	Z
Open	L	H

(1) H = high level, L = low level, X = irrelevant,
Z = high impedance (off),
Open = input disconnected or connected driver off

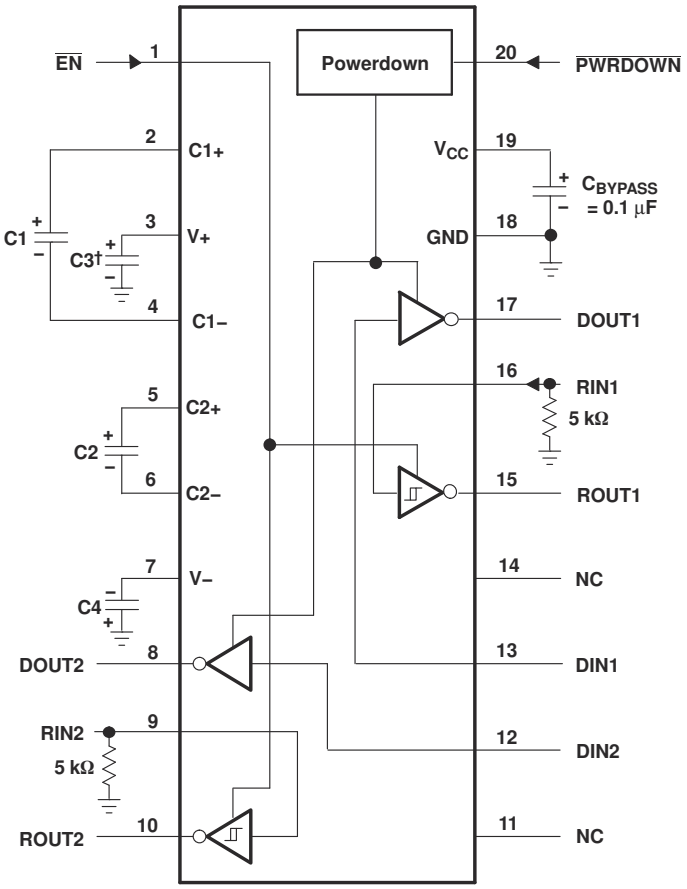
8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

8.2 Typical Application



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.
B. NC – No internal connection
C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

図 8-1. Typical Operating Circuit and Capacitor Values

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.2 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

リンクされているコンテンツは、各寄稿者により「現状のまま」提供されるものです。これらはテキサス・インスツルメンツの仕様を構成するものではなく、必ずしもテキサス・インスツルメンツの見解を反映したものではありません。テキサス・インスツルメンツの使用条件を参照してください。

9.3 商標

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

9.4 静電気放電に関する注意事項

この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.5 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision D (December 2024) to Revision E (December 2024)	Page
• データシート全体にわたって VSSOP (DSG) パッケージを VSSOP (DGS) パッケージに変更	1

Changes from Revision C (January 2023) to Revision D (December 2024)	Page
• 「製品情報」表を「パッケージ情報」表に変更	1
• データシートに VSSOP (DSG) パッケージを追加	1
• Added Note 2 to the *ESD Ratings, IEC Specifications*	4

Changes from Revision B (August 2021) to Revision C (January 2023)	Page
• Changed the *ESD Ratings - IEC Specifications* table note to include the DB package	4
• Changed the values of $R_{\theta JA}$ in the *Thermal Information* table for the DB package	5

Changes from Revision A (September 2009) to Revision B (August 2021) **Page**

- 「*アプリケーション*」の一覧を更新 1
- 「注文情報」表を削除 1
- 「*製品情報*」表、「*ピン構成および機能*」、「*詳細説明*」セクション、「*アプリケーションと実装*」セクションを追加 1
- Deleted the Package thermal impedance from the *Absolute Maximum Ratings* 4
- Changed the *ESD Ratings* table 4
- Added the *ESD Ratings - IEC Specifications* table 4
- Added the *Thermal Information* table 5
- Changed the value of $R_{\theta JA}$ for PW package (previously in the *Absolute Maximum Ratings* table), and added additional thermal parameters for all packages in the *Thermal Information* table 5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
MAX3222ECDB	Obsolete	Production	SSOP (DB) | 20	-	-	Call TI	Call TI	0 to 70	MP222EC
MAX3222ECDBR	Obsolete	Production	SSOP (DB) | 20	-	-	Call TI	Call TI	0 to 70	MP222EC
MAX3222ECDW	Obsolete	Production	SOIC (DW) | 20	-	-	Call TI	Call TI	0 to 70	MAX3222EC
MAX3222ECDWR	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3222EC
MAX3222ECDWR.A	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3222EC
MAX3222ECDWRG4	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EC
MAX3222ECDWRG4.A	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EC
MAX3222ECPWR	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC
MAX3222ECPWR.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MP222EC
MAX3222EIDBR	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIDBR.A	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIDBRG4	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIDBRG4.A	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIDGSR	Active	Production	VSSOP (DGS) | 20	5000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	222EI
MAX3222EIDGSR.A	Active	Production	VSSOP (DGS) | 20	5000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	222EI
MAX3222EIDW	Obsolete	Production	SOIC (DW) | 20	-	-	Call TI	Call TI	-40 to 85	MAX3222EI
MAX3222EIDWR	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EI
MAX3222EIDWR.A	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3222EI
MAX3222EIPWR	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIPWR.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIPWRG4	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI
MAX3222EIPWRG4.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP222EI

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

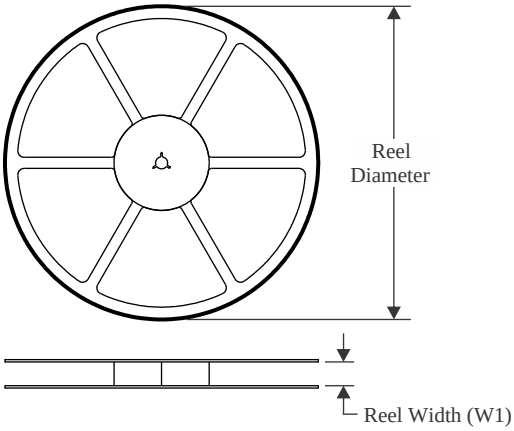
(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

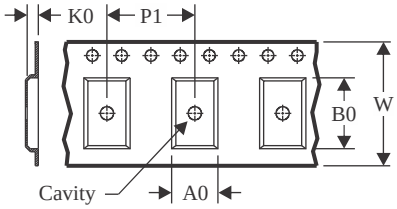
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

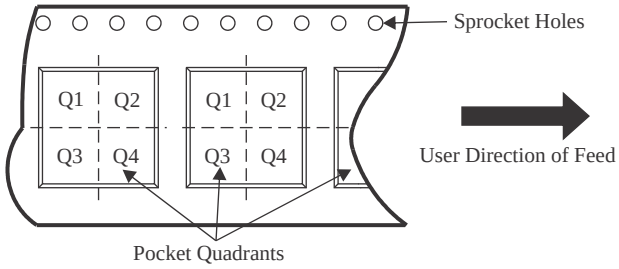


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

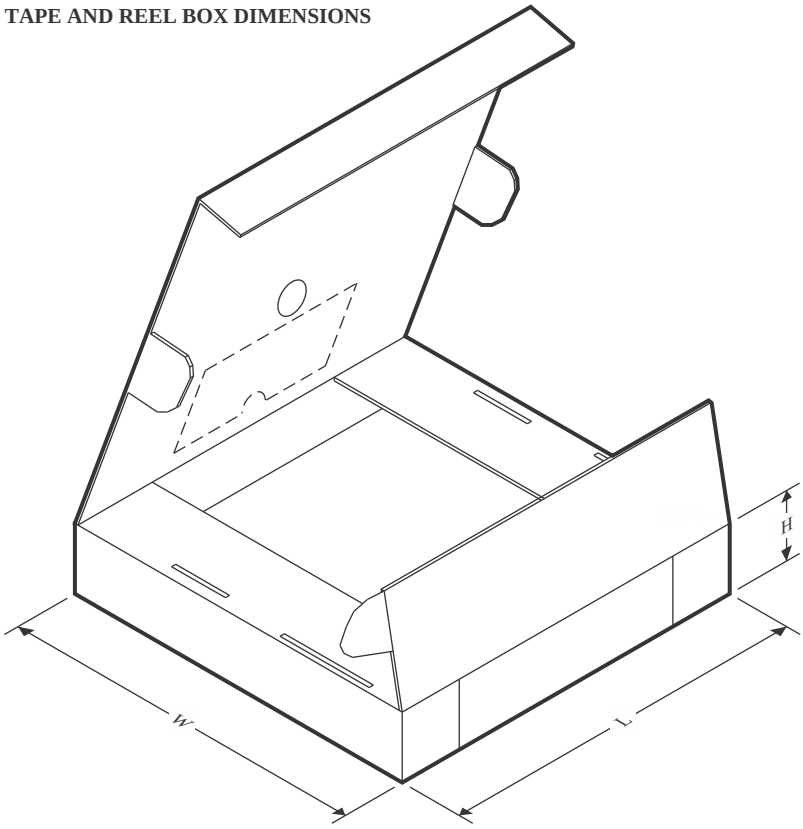
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

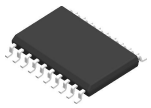
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3222ECDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3222ECDWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3222ECPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
MAX3222EIDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3222EIDBRG4	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3222EIDGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
MAX3222EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3222EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
MAX3222EIPWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX3222ECDWR	SOIC	DW	20	2000	356.0	356.0	45.0
MAX3222ECDWRG4	SOIC	DW	20	2000	356.0	356.0	45.0
MAX3222ECPWR	TSSOP	PW	20	2000	353.0	353.0	32.0
MAX3222EIDBR	SSOP	DB	20	2000	353.0	353.0	32.0
MAX3222EIDBRG4	SSOP	DB	20	2000	353.0	353.0	32.0
MAX3222EIDGSR	VSSOP	DGS	20	5000	353.0	353.0	32.0
MAX3222EIDWR	SOIC	DW	20	2000	356.0	356.0	45.0
MAX3222EIPWR	TSSOP	PW	20	2000	353.0	353.0	32.0
MAX3222EIPWRG4	TSSOP	PW	20	2000	353.0	353.0	32.0

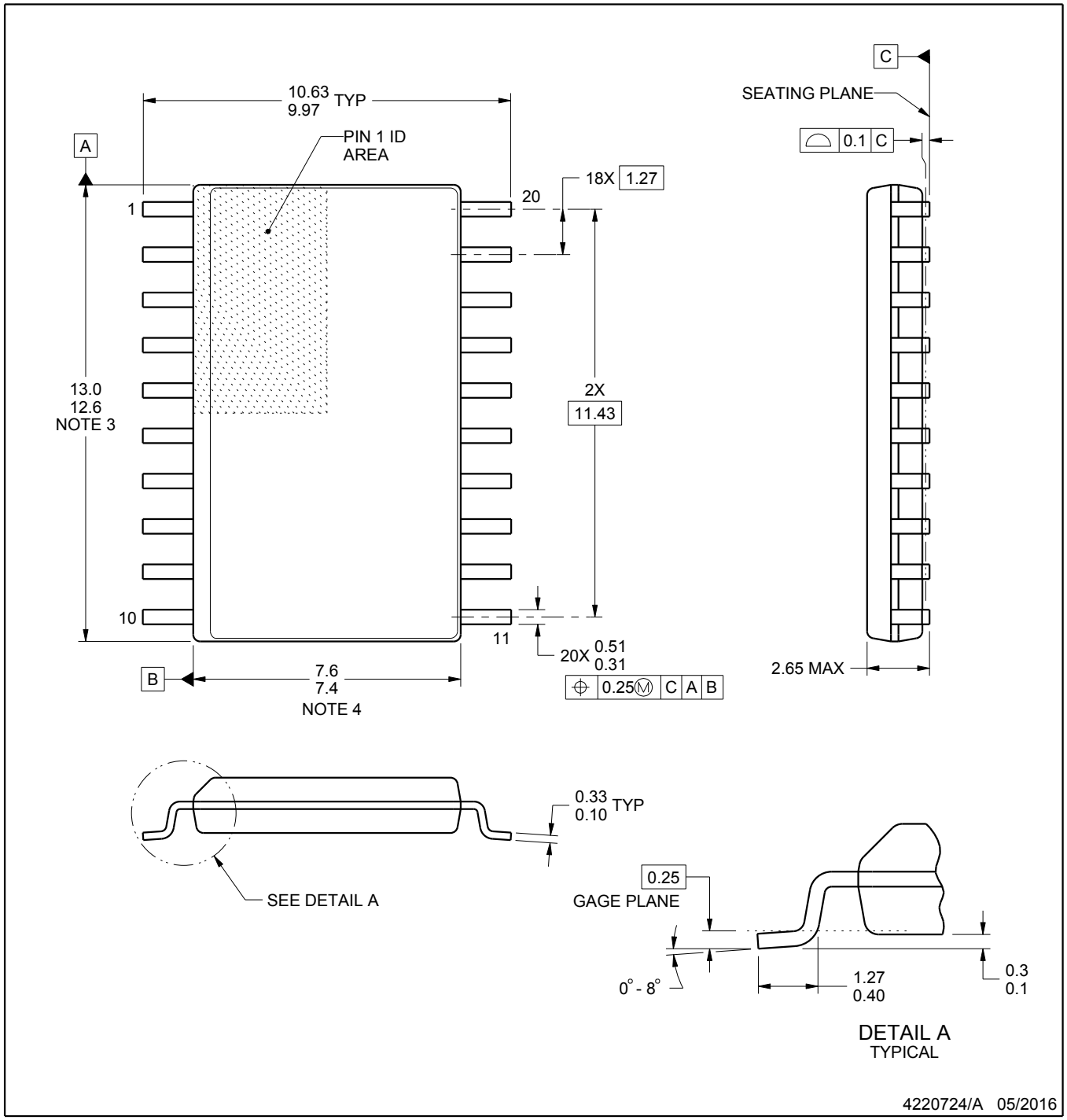


PACKAGE OUTLINE

DW0020A

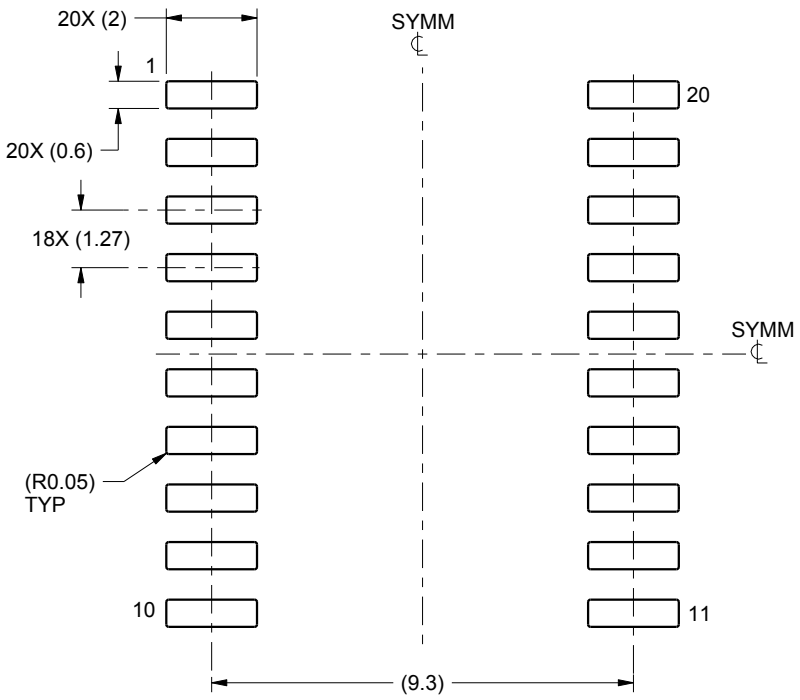
SOIC - 2.65 mm max height

SOIC

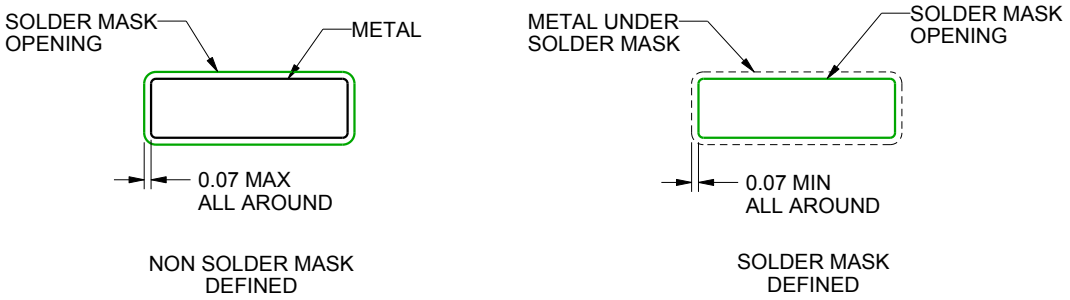


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:6X

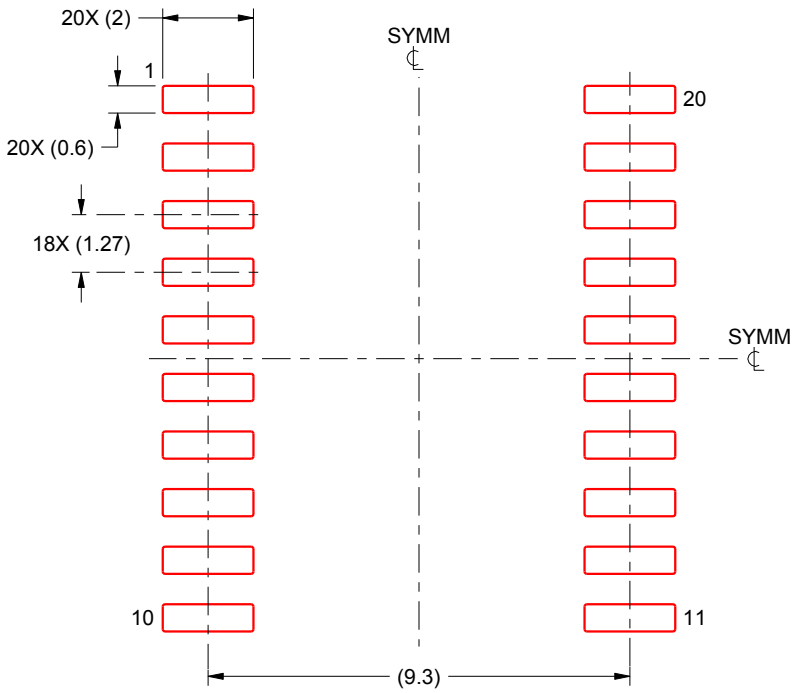


SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

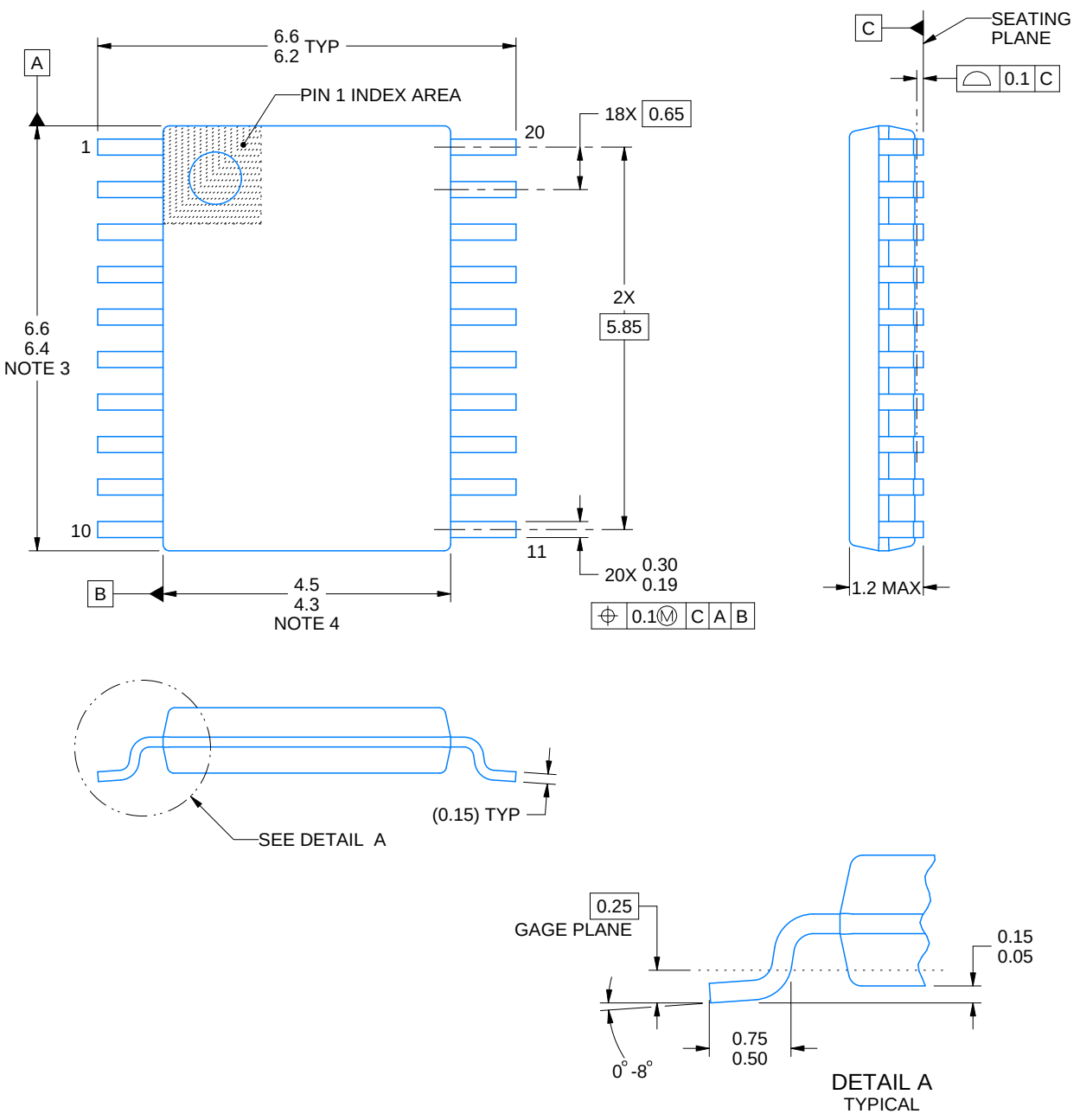
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

PW0020A

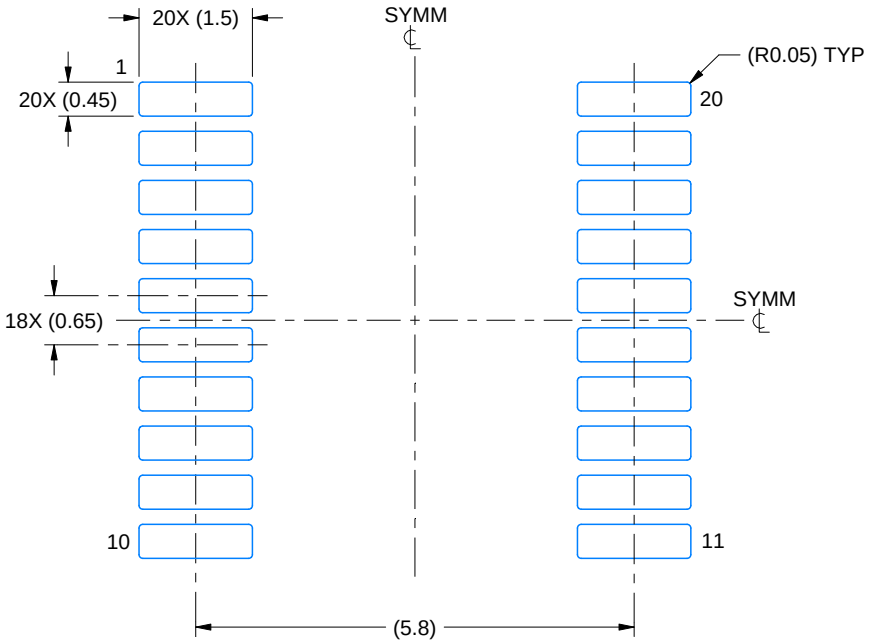
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



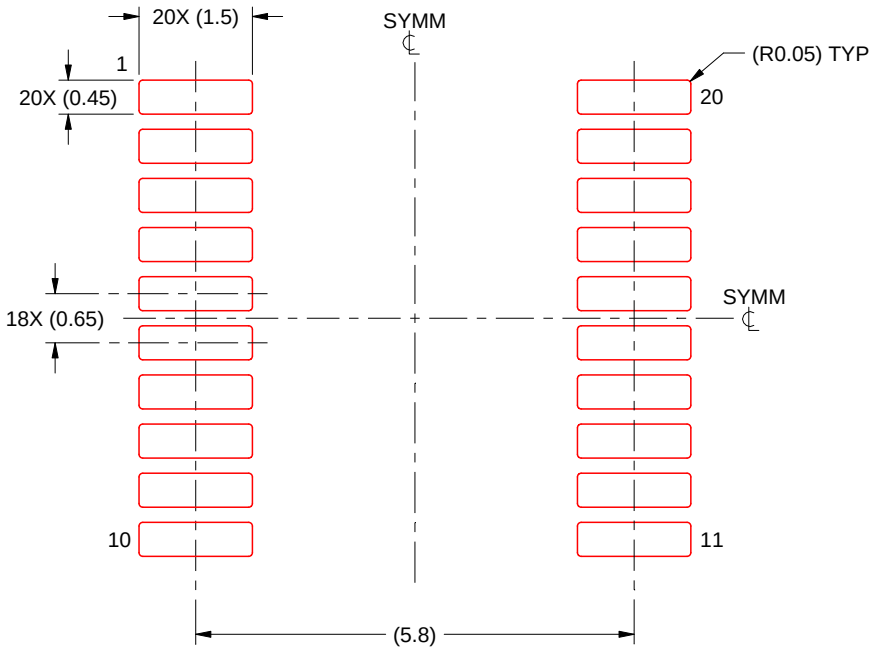
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

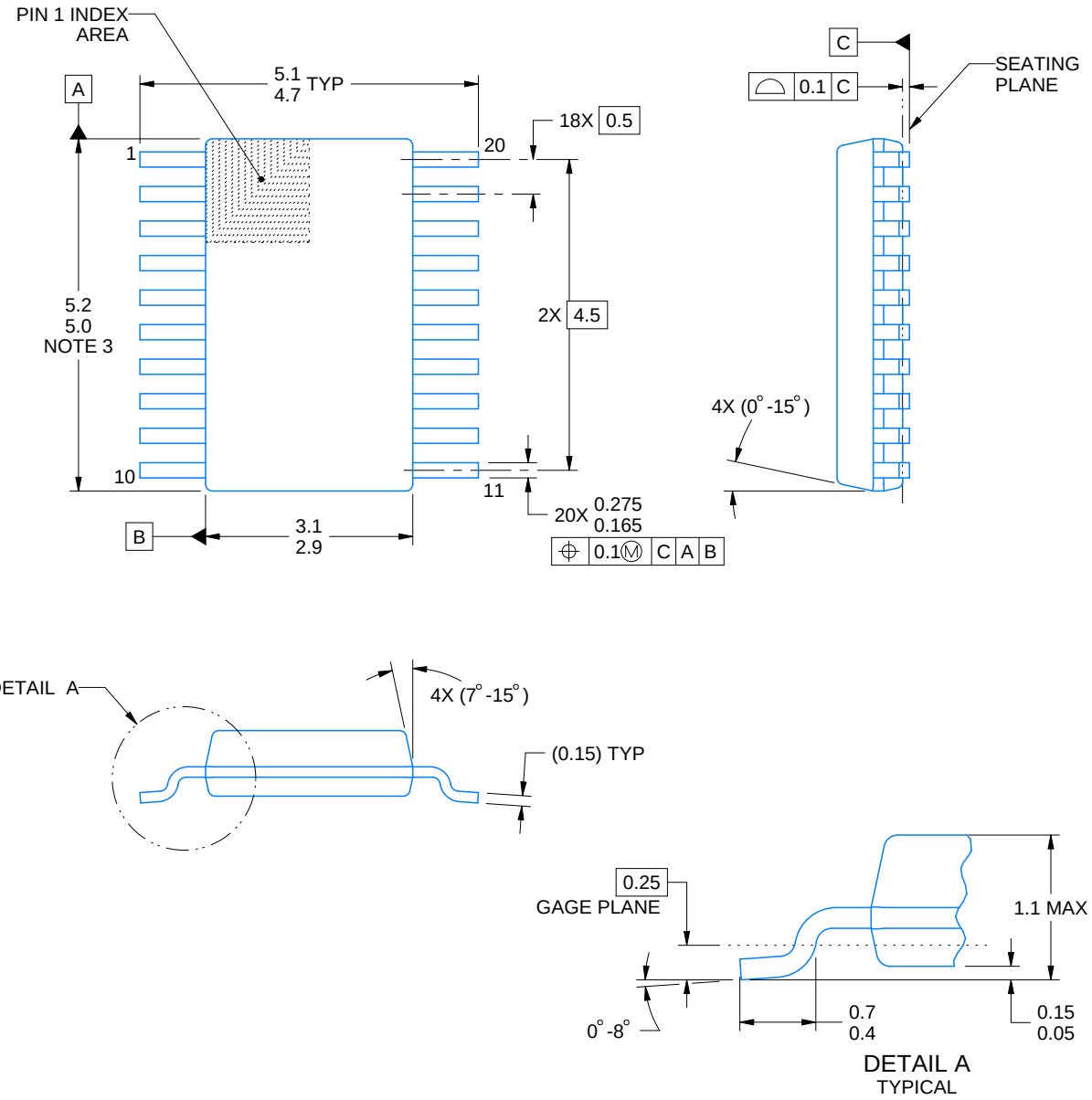
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DGS0020A

VSSOP - 1.1 mm max height

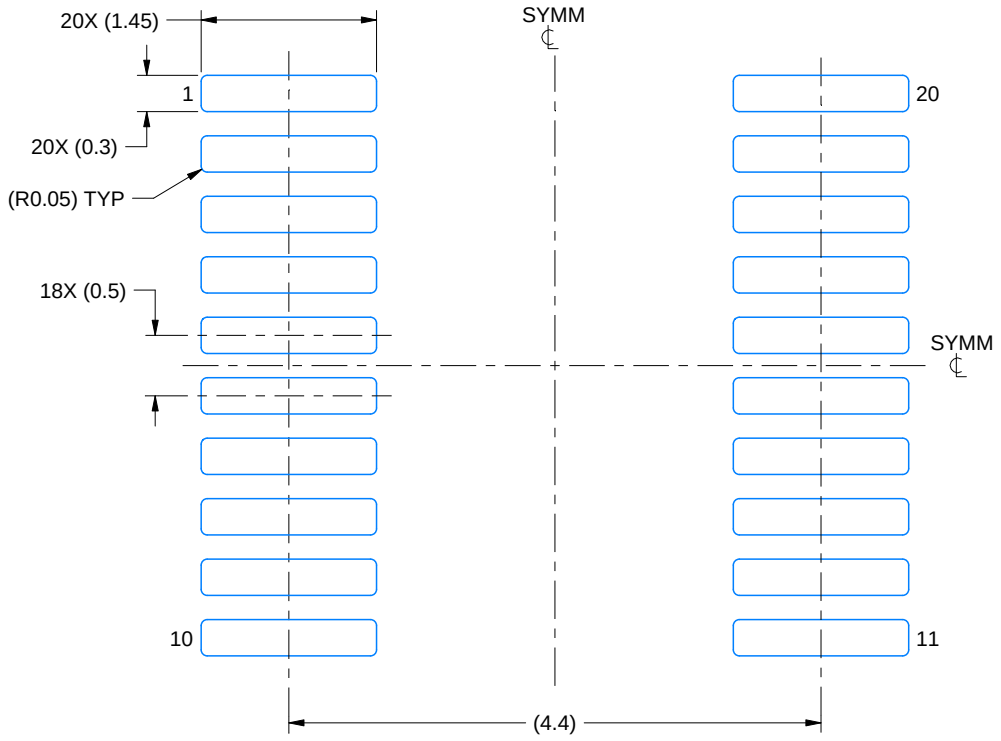
SMALL OUTLINE PACKAGE



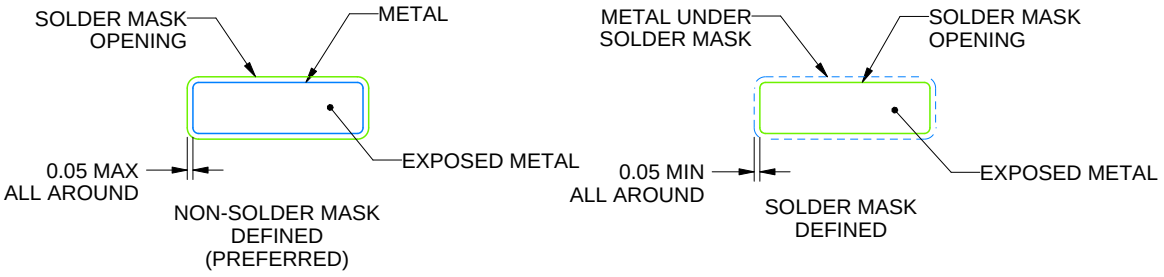
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. No JEDEC registration as of September 2020.
5. Features may differ or may not be present.



LAND PATTERN EXAMPLE
SCALE: 16X

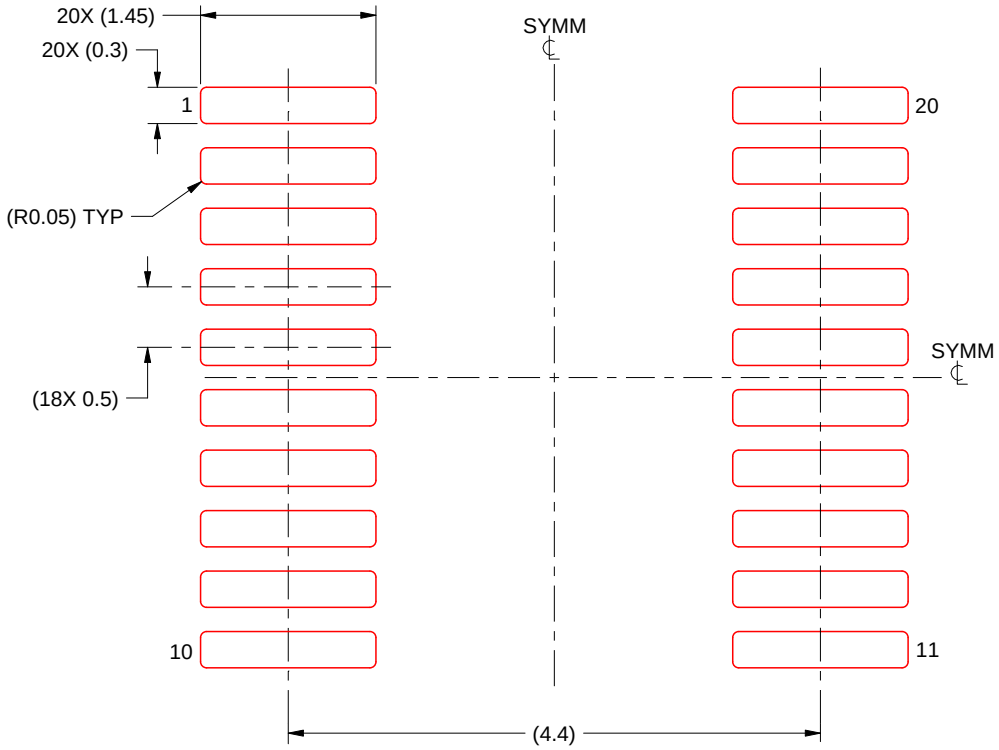


SOLDER MASK DETAILS

4226367/A 10/2020

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 16X

4226367/A 10/2020

NOTES: (continued)

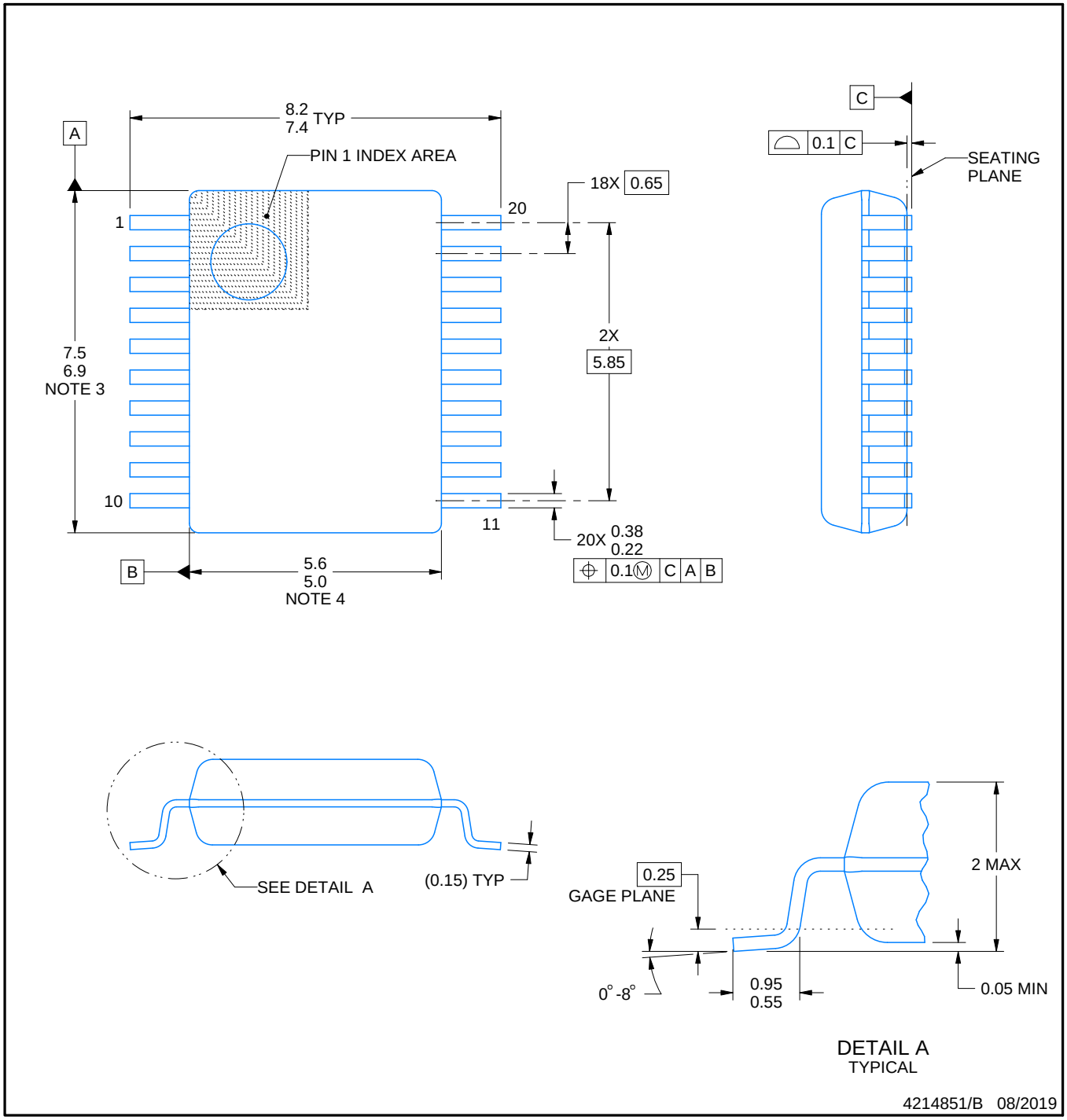
11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DB0020A

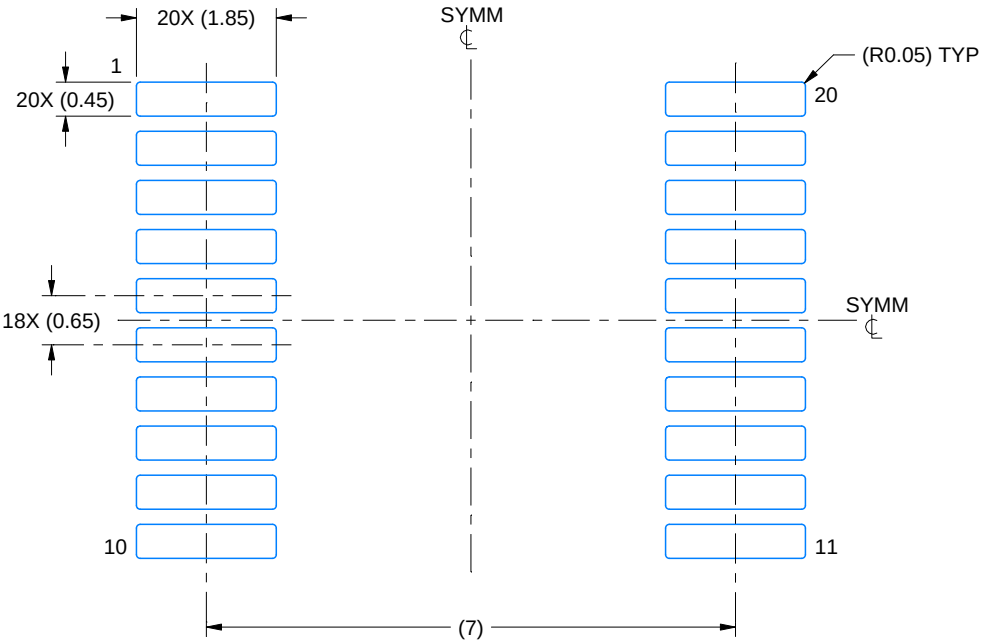
SSOP - 2 mm max height

SMALL OUTLINE PACKAGE

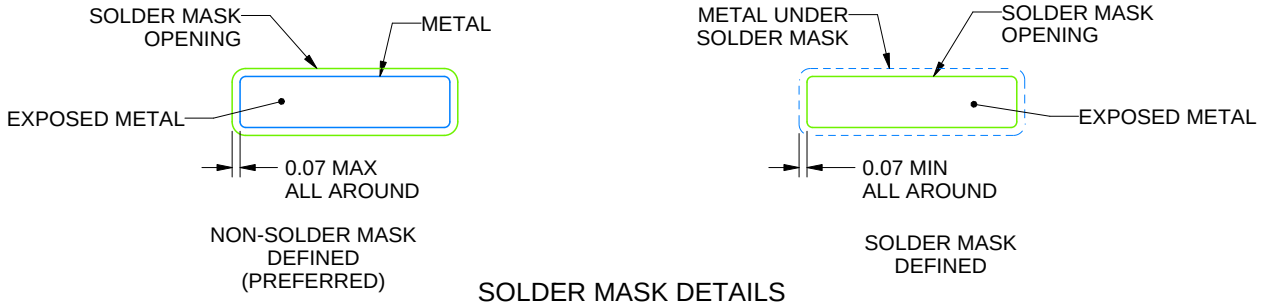


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4214851/B 08/2019

NOTES: (continued)

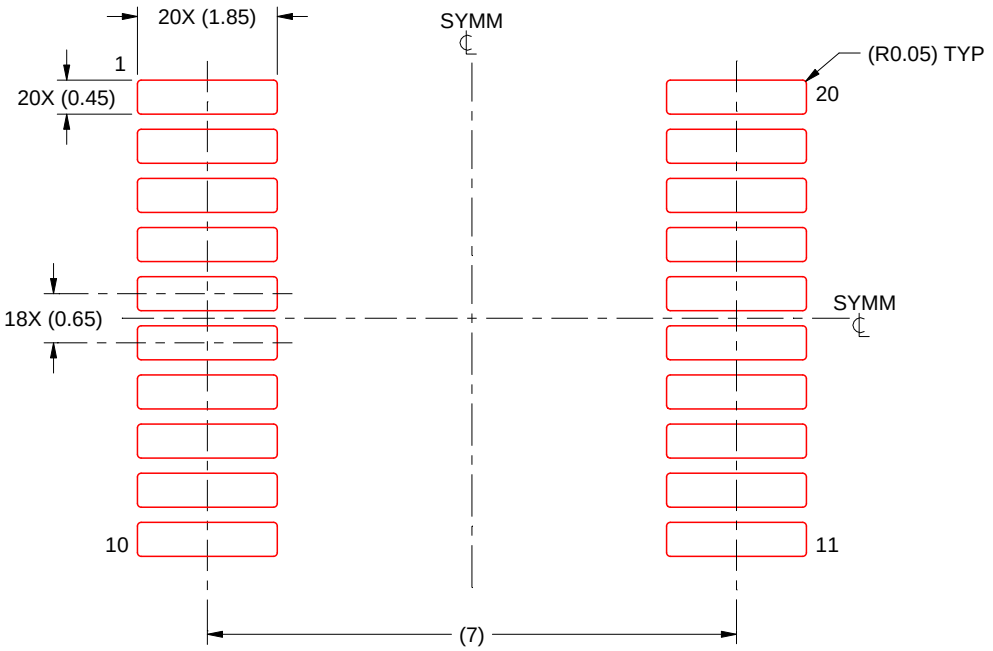
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214851/B 08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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